

N-Channel Enhancement Mode Power MOSFET

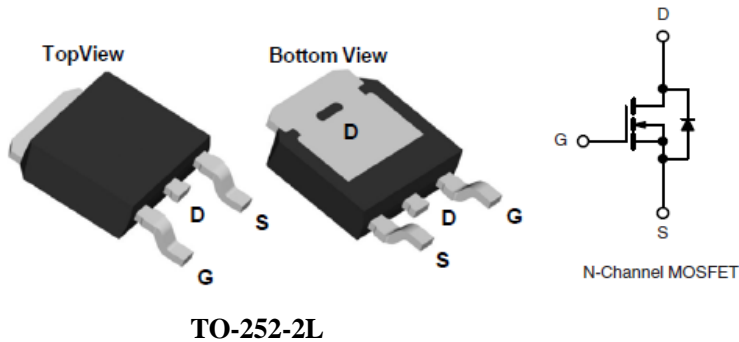
● Features

| V_{DS} | $R_{DS(ON)TYP}$ | I_D |
|----------|--------------------|-------|
| 60V | 14 m Ω @10V | 50A |

● General Description

- Power Switching Application
- Hard Switched and High Frequency circuits
- Uninterruptible power supply

● Pin Configurations



● Absolute Maximum Ratings @ $T_A=25^{\circ}\text{C}$ unless otherwise noted

| Parameter | | Symbol | Ratings | Unit |
|--|---------------------------|---------------|----------|--------------------|
| Drain-Source Voltage | | V_{DSS} | 60 | V |
| Gate-Source Voltage | | V_{GSS} | ± 20 | V |
| Drain Current (Continuous) *AC | $T_C=25^{\circ}\text{C}$ | I_D | 50 | A |
| | $T_C=100^{\circ}\text{C}$ | | 35 | |
| Drain Current (Pulse) *B | | I_{DM} | 200 | A |
| Avalanche energy $L=0.5\text{mH}$ | | E_{AS} | 300 | mJ |
| Power Dissipation | $T_C=25^{\circ}\text{C}$ | P_D | 85 | W |
| Operating Temperature/ Storage Temperature | | T_J/T_{STG} | -55~150 | $^{\circ}\text{C}$ |

● Thermal Resistance Ratings

| Parameter | | Symbol | Maximum | Unit |
|----------------------------------|--------------|------------|---------|-----------------------------|
| Maximum Junction-to-Case (Drain) | Steady State | R_{thJC} | 1.8 | $^{\circ}\text{C}/\text{W}$ |

Electrical Characteristics

$T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|----------------------------------|---------------|---|-----|------|-----------|------------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$ | 60 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 48V, V_{GS} = 0V$ | -- | -- | 1 | μA |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_{DS} = 250\mu A$ | 1 | -- | 3 | V |
| Gate Leakage Current | I_{GSS} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | -- | -- | ± 100 | nA |
| Drain-Source On-state Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 20A$ | -- | 14 | 20 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS} = 5V, I_D = 20A$ | 18 | -- | -- | S |
| Diode Forward Voltage | V_{SD} | $I_{SD} = 20A, V_{GS} = 0V$ | -- | -- | 1.2 | V |
| Diode Forward Current | I_S | $T_C = 25^\circ\text{C}$ | -- | -- | 50 | A |
| Switching | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 30V, I_D = 20A,$ $V_{GS} = 10V$ | -- | 50 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 6 | -- | nC |
| Gate-Drain Charge | Q_{gd} | | -- | 15 | -- | nC |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DS} = 30V, R_G = 3\Omega,$ $V_{GS} = 10V, R_L = 6.7\Omega$ | -- | 7.4 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 5.1 | -- | ns |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 28.2 | -- | ns |
| Turn-Off Fall Time | t_f | | -- | 5.5 | -- | ns |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 30V, V_{GS} = 0V, f = 1.0\text{MHz}$ | -- | 2050 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 158 | -- | pF |
| Reverse Transfer Capacitance | C_{rss} | | -- | 120 | -- | pF |

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

Typical Electrical and Thermal Characteristics

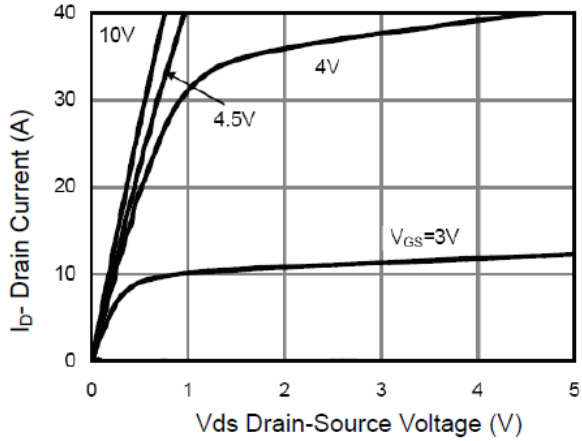


Figure 1 Output Characteristics

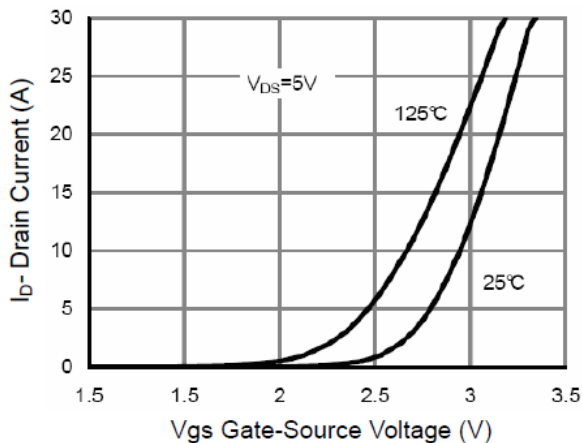


Figure 2 Transfer Characteristics

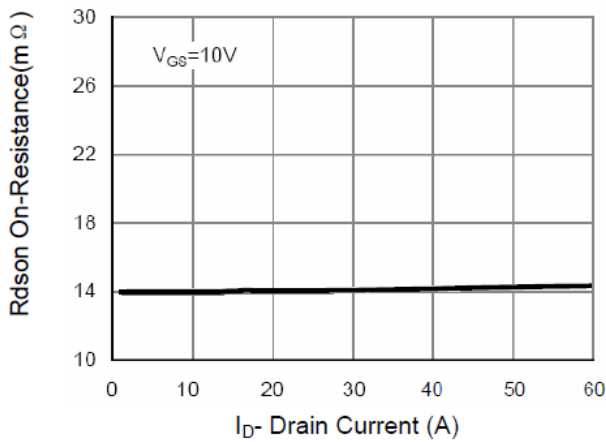


Figure 3 Rdson- Drain Current

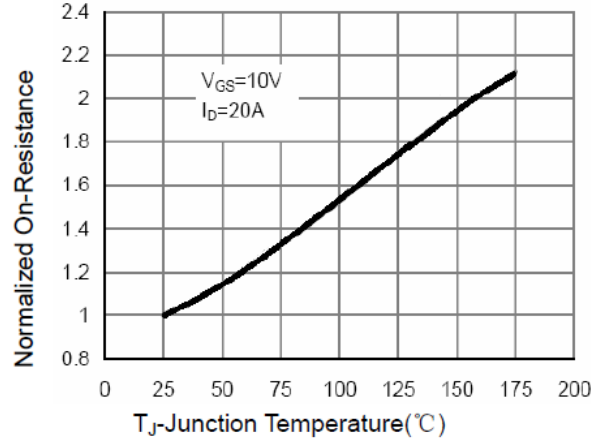


Figure 4 Rdson-Junction Temperature

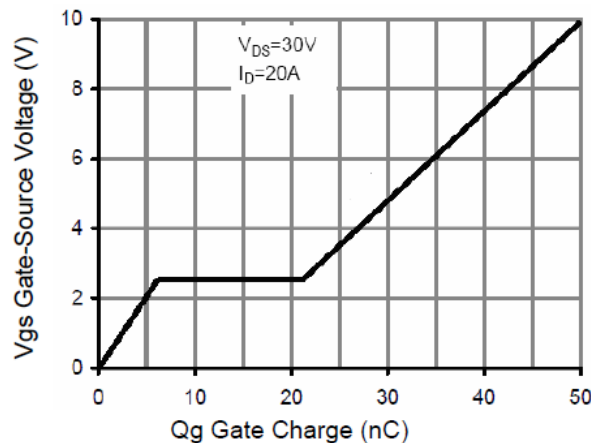


Figure 5 Gate Charge

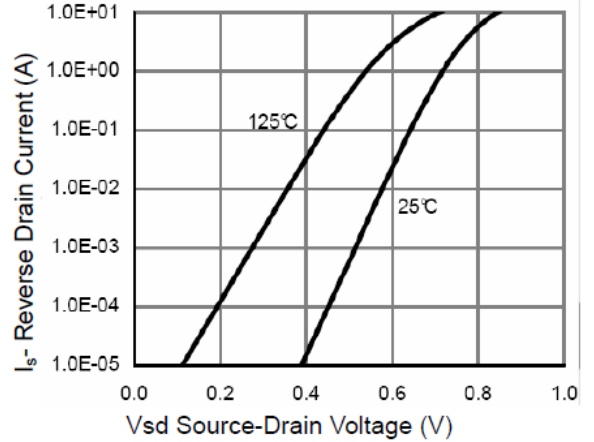


Figure 6 Source- Drain Diode Forward

Typical Electrical and Thermal Characteristics

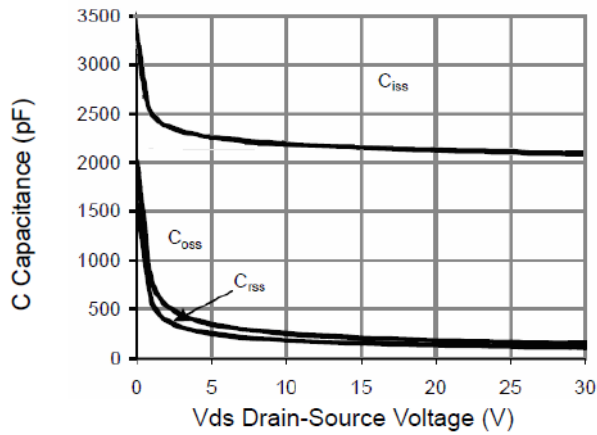


Figure 7 Capacitance vs Vds

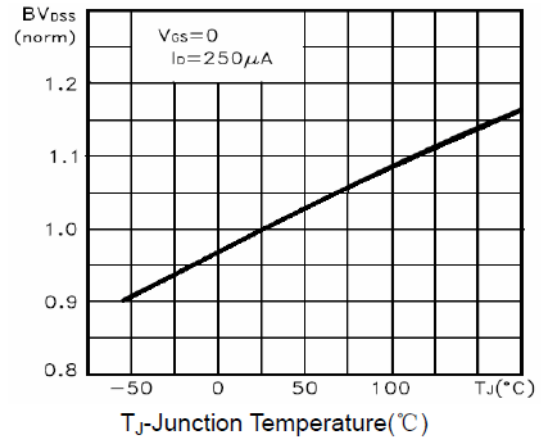


Figure 9 BV_{DSS} vs Junction Temperature

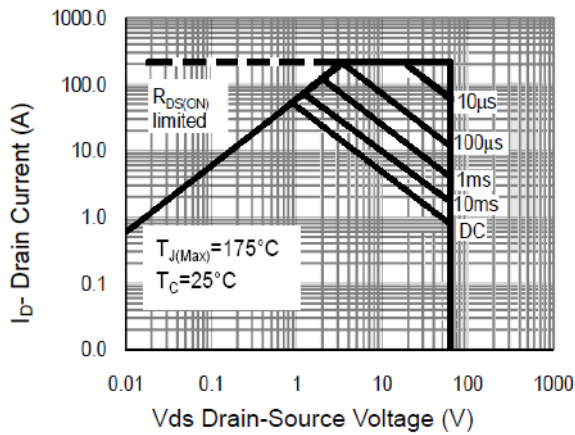


Figure 8 Safe Operation Area

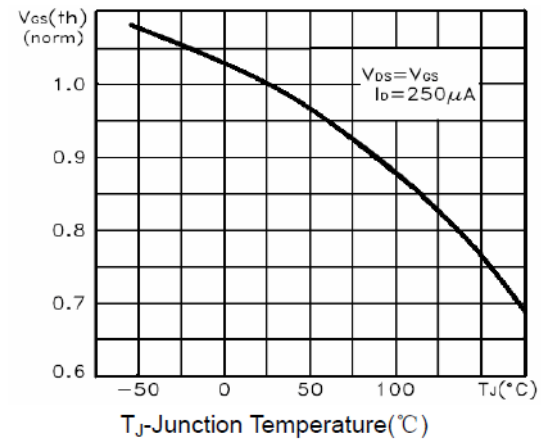


Figure 10 $V_{GS(th)}$ vs Junction Temperature

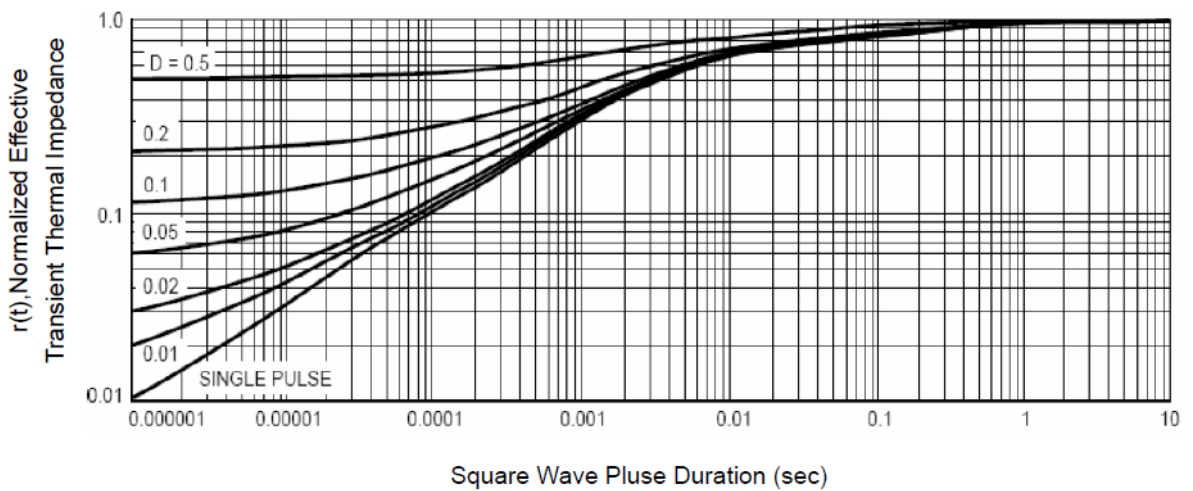
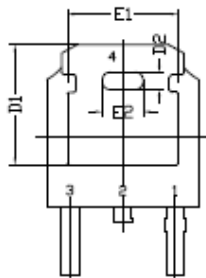
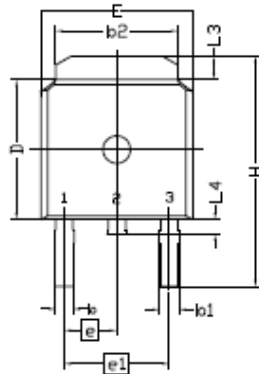


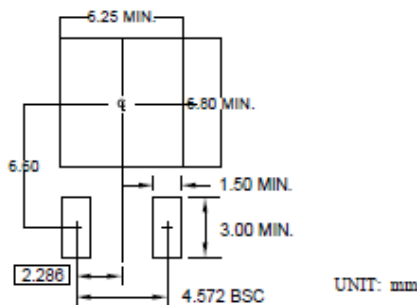
Figure 11 Normalized Maximum Transient Thermal Impedance

Package Information

T0252(DPAK) PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MILS.
2. DIMENSION L IS MEASURED IN GAUGE PLANE
3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
5. REFER TO JEDEC TO-252 (AA)

| SYMBOL | DIMENSION IN MILLIMETERS | | | DIMENSIONS IN INCHES | | |
|--------|--------------------------|--------|--------|----------------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 2.184 | 2.286 | 2.388 | 0.086 | 0.090 | 0.094 |
| A1 | 0.000 | --- | 0.127 | 0.000 | --- | 0.005 |
| A2 | 0.889 | 1.041 | 1.143 | 0.035 | 0.041 | 0.045 |
| b | 0.635 | 0.762 | 0.889 | 0.025 | 0.030 | 0.035 |
| b1 | 0.762 | 0.840 | 1.143 | 0.030 | 0.033 | 0.045 |
| b2 | 4.953 | 5.340 | 5.461 | 0.195 | 0.210 | 0.215 |
| c | 0.450 | 0.508 | 0.610 | 0.018 | 0.020 | 0.024 |
| c1 | 0.450 | 0.508 | 0.610 | 0.018 | 0.020 | 0.024 |
| D | 5.969 | 6.096 | 6.223 | 0.235 | 0.240 | 0.245 |
| D1 | 5.210 | 5.249 | 5.380 | 0.205 | 0.207 | 0.212 |
| D2 | 0.862 | 0.762 | 0.862 | 0.026 | 0.030 | 0.034 |
| E | 6.350 | 6.604 | 6.731 | 0.250 | 0.260 | 0.265 |
| E1 | 4.318 | 4.826 | 4.901 | 0.170 | 0.190 | 0.193 |
| E2 | 1.678 | 1.778 | 1.878 | 0.066 | 0.070 | 0.074 |
| e | 2.286 BSC | | | 0.090 BSC | | |
| e1 | 4.572 BSC | | | 0.180 BSC | | |
| H | 9.398 | 10.033 | 10.414 | 0.370 | 0.395 | 0.410 |
| L | 1.270 | 1.520 | 2.032 | 0.050 | 0.060 | 0.080 |
| L1 | 2.921 REF. | | | 0.115 REF. | | |
| L2 | 0.408 | 0.508 | 0.608 | 0.016 | 0.020 | 0.024 |
| L3 | 0.889 | 1.016 | 1.270 | 0.035 | 0.040 | 0.050 |
| L4 | 0.635 | --- | 1.016 | 0.025 | --- | 0.040 |